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cont*

fabricating a copper (Cu) bond pad from the interconnect material;  
depositing a tantalum (Ta) layer onto the substrate and over the bond pad;  
patterning and etching the tantalum (Ta) layer; and  
bonding an aluminum (Al) wire to the tantalum (Ta) layer over the bond pad;  
wherein a portion of the tantalum (Ta) layer forms a metallurgical bond with the copper  
(Cu) bond pad, and another portion of the tantalum (Ta) layer forms a tantalum aluminide ( $TaAl_3$ )  
compound to bond with the aluminum wire.

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